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- (54) **Title:** TOPOLOGICAL SEMI-METAL INTERCONNECTS
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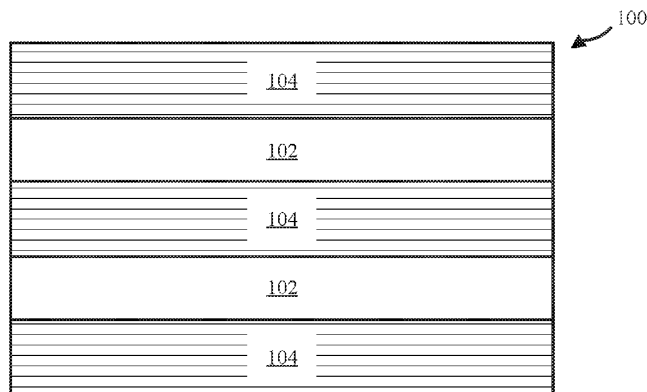


FIG. 2B

(57) **Abstract:** Provided is a method for fabricating an interconnect. The method comprises forming a topological semi-metal layer. The method further comprises patterning the topological semi-metal layer to form one or more interconnects. The method further comprises forming a dielectric layer between the one or more interconnects. The method further comprises forming a hermetic dielectric cap layer on top of the one or more interconnects and the dielectric layer.

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